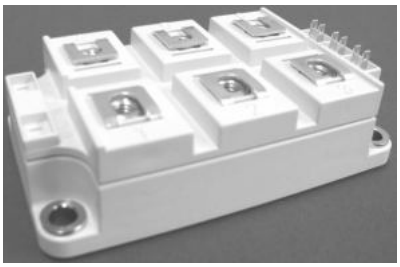
SKKR 400/0.2 BVR



SEMITRANS™ 5

Shunt Modules

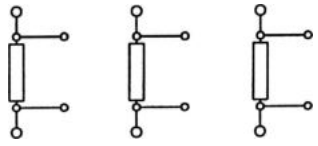
SKKR 400/0.2 BVR

Features

- Low inductance value
- Excellent long term stability
- Isolated copper baseplate using DCB (Direct Copper Bonding) Technology
- Large clearance (13 mm) and creepage distance (20 mm)
- Using BVR Shunts for extended lifetime

Typical Applications

- Current sensor for frequency converter



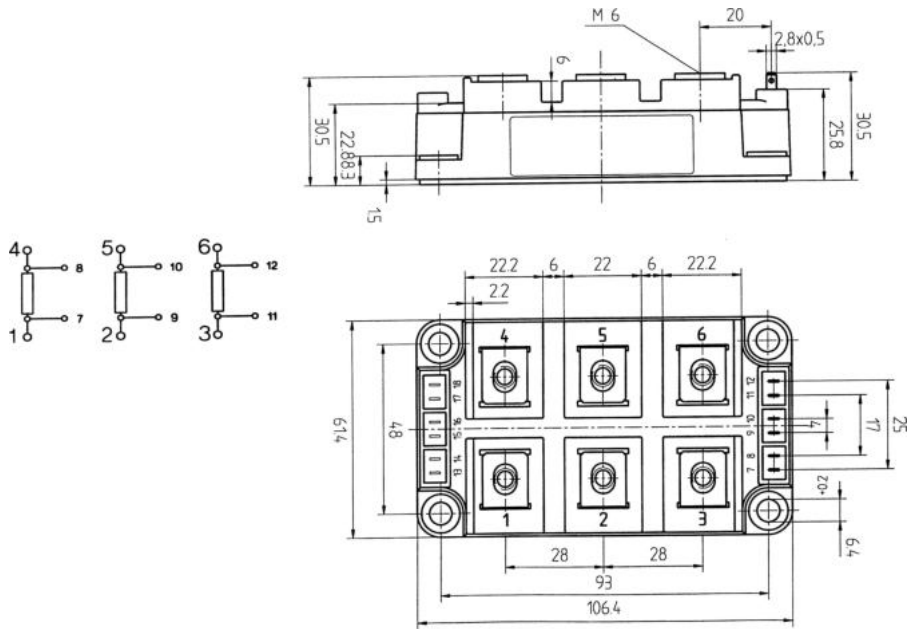
Absolute Maximum Ratings	T_c = 25 °C, unless otherwise specified		
Symbol	**Conditions**	**Values**	**Units**
I_{DCmax}	T_{shunt} = 150 °C; T_C = 25(80) °C	270 (200)	A
I_{SC}	t_{sc} = 10 µs	700	A
R_{shunt}	Toleranz = ± 5%	0,53	mΩ
$T_{cr(shunt)}$	temperature coefficient (20-60) °C	50	ppm/K
P_{tot}	per shunt; T_C = 25(80) °C	36 (20)	W
T_{stg}		- 40 ... + 125	°C
V_{isol}	AC, 1 min., I_{iso} = 1 mA	2500	V
humidity	IEC-EN 60 721-3-3		
climate	IEC 68 T.1	40/126/56	

Characteristics	T_c = 25 °C, unless otherwise specified				
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Units**
V_{7-8}	IDC = 400 A; TC = 25(125) °C	210	213 (211)	216	mV
V_{9-10}	IDC = 400 A; TC = 25(125) °C	210	213 (211)	216	mV
V_{11-12}	IDC = 400 A; TC = 25(125) °C	210	213 (211)	216	mV
$C_{shunt/C}$			280		pF
L_{tray}	I_C = 100 A; V_{CE} = 600 V (turn off single IGBT)			0,4	nF
Thermal characteristics					
$R_{th(j-c)}$				7,0	K/W

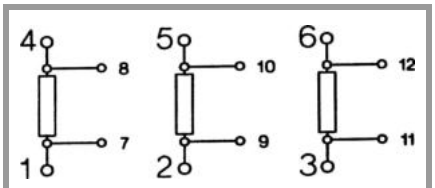
Mechanical Data						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
M_1	to heatsink, SI Units	(M6)	3		5	Nm
	to heatsink, US Units		27		44	lb.in.
M_2	to heatsink, SI Units	(M6)	2,5		5	Nm
	to heatsink, US Units		22		44	lb.in.
a					5x9,81	m/s²
$_w$					420	g

SKKR 400/0.2 BVR

Dimensions in mm



Case D 97



SKKR **Case D 97**

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.